



Features

- Mechanically and spectrally matchend to the infrared emitting LED LAMP.
- Navy Blue Lens
- Rohs compliant.

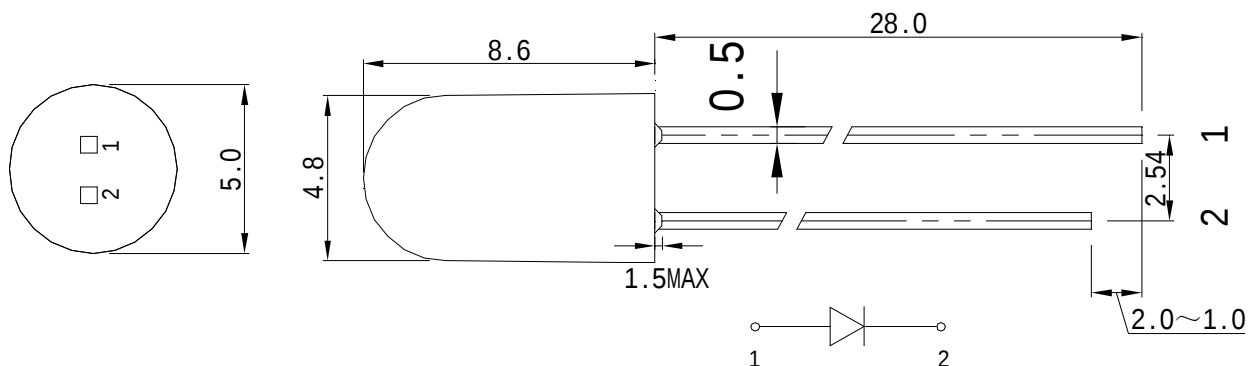
HL-503PD4FN-T-B2



Package Dimensions

Description

Made with PIN silicon photo-diode chips.



Tolerance Grade	Dimension Tolerance (UNIT:mm)			
	0.5~3	3~6	6~30	30~120
	±0.1	±0.2	±0.3	±0.5

HL-503PD4FN-T-B2
Electrical / Optical Characteristics at TA=25°C

Parameter	Symbol	Min	Typ	Max	Units	Test Conditions
Forward Voltage	V_F	0.5	-	1.3	V	$I_F=10\text{mA}$
Reverse Breakdown Voltage	V_{BR}	35	-	-	V	$I_R=100\text{ }\mu\text{A}$
Reverse Dark Current	I_D	-	2	10	nA	$V_R=10\text{V}$
Light Current	I_L	-	11	-	μA	$V_R=5\text{V}$ Has $1\text{mw}/\text{cm}^2@940\text{nm}$
Peak Sening Wavelength	λ_p	-	940	-	nm	
Junction Capacitance	C_J	-	14	-	P_F	$V_R=3\text{V}$ $F=1\text{MHz}$

Absolute Maximum ratings at Ta=25°C

Parameter	Max Ratings
Power Dissipation at (or below) 25°C Free Air Temperature	100mW
Operating Temperature Range	-30°C~80°C
Storage Temperature Range	-30°C~80°C
Lead Soldering Temperature (>3mm for 5sec)	260°C



Soldering:

1. Manual Of Soldering

The temperature of the iron tip should not be higher than 300°C and Soldering within 3 seconds per solder-land is to be observed.

2. DIP soldering (Wave Soldering):

Preheating: 120°C~150°C, within 120~180 sec.

Operation heating: 245°C ± 5°C within 5 sec. 260°C (Max)

Gradual Cooling (Avoid quenching).

